

**THE EXPOSURE DEPENDENCE AND EMISSION SPECTRUM OF  
CHEMILUMINESCENCE PRODUCED DURING THE OXIDATION OF Si(111) BY O<sub>2</sub>**

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**ABSTRACT**

Chemiluminescence produced during the low pressure oxidation of a Si(111) surface by O<sub>2</sub> has been investigated. Carefully cleaned and annealed samples yield chemiluminescence at pressures as low as  $6 \times 10^{-7}$  torr, corresponding to a peak chemiluminescence yield of  $2.2 \times 10^{-7}$  photons per incident molecule and comparing favorably with the value of  $1 \times 10^{-7}$  measured by Bruce and Comas (ref.1). The evolution of the emission shows a hyperbolic decrease in time at pressures above  $1 \times 10^{-4}$  torr but becomes more complex at the lowest exposures studied. The spectrally broad chemiluminescence was dispersed at medium resolution and recorded with an Optical Multichannel Analyzer in an attempt to identify and characterize the energy content of the emitting species.

**REFERENCES**

1. L. E. Bruce and J. Comas, *J. Chem. Phys.*, 54 (1971) 2771